PM007N100CM

100V 60A 7.8mΩ Single N channel Trench MOSFET with Normal Diode

PowerCubeSemi, Inc.
Potential · Convergence · Smart

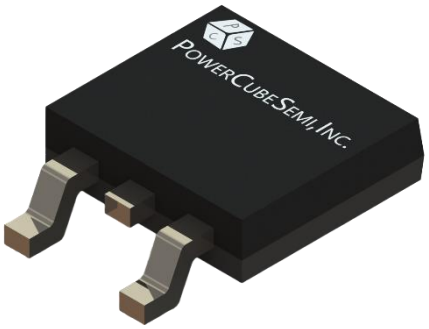
Features

Si Single N channel Trench MOSFET

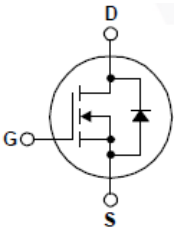
- Rated to 100V at 60Amps @T_J = 25℃
- Max $R_{DS(on)}$ = 7.8 mΩ
- Typ $R_{DS(on)}$ = 6.8 mΩ
- Gate Charge(Typ. Q_g=72 nC)
- Very low on-resistance $R_{DS(on)}$
- 100% Rg Tested
- 100% Avalanche Tested

Application

- Synchronous Rectification
- Switching Applications



PKG type : TO-252



Halogen-Free

RoHS

Description

PM002N100CM uses advanced PowerCubeSemi's middle voltage MOSFET technology, which provides high performance in on-state resistance, fast switching performance, and excellent quality. PM002N100CM is suitable device for Motor Drive applications and general purpose applications.

Absolute Maximum Ratings

Symbol	Parameter	Test Condition	Value	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V, I_D=250μA	100	V
I_D	Drain Current	T_c=25℃	60	A
I_{DM}	Pulsed Drain Current	Pulse width limited by junction temperature	240	A
V_{GS}	Gate-Source Voltage		±20	V
E_{AS}	Single Pulsed Avalanche Energy	I_{AS}=15A, V_{GS}=10Ω V_{DD}=50V, L=1.0mH	113	mJ
P_d	Power Dissipation	T_C=25℃	96	W
T_j	Operating Junction Temperature		150	℃
T_{stg}	Storage Temperature		-55 to 150	℃

Package Marking and Ordering Information

Device Marking	Device	Package	Packing Method	Tape width	Quantity
PM002N100CM	PM002N100	DPAK	Tube & Reel	-	-

Electrical Characteristics of Si MOSFET

Symbol	Parameter	Test Condition	Numerical			Unit
			Min	Typ.	Max.	
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0V, I_D = 250μA, T_J = 25°C	100	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 100V, V_{GS} = 0V	-	-	1	μA
I_{GSS}	Gate-Source Leakage Current	V_{GS} = ±20V, V_{DS} = 0V	-	-	±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} =V_{GS}, I_D = 250μA	1.2	1.6	2.2	V
$R_{DS(ON)}$	Static Drain-Source on state resistance	V_{GS} = 10V, I_D = 20A	-	6.8	7.8	mΩ
g_{FS}	Forward Transconductance	V_{DS} =10V, I_D = 20A	-	92	-	S
$t_{d(on)}$	Turn-on Delay time	V_{DD} = 50 V, I_D = 20A, V_{GS} = 10 V, R_G = 3Ω	-	18	-	ns
T_r	Turn-on Rise time		-	7	-	
$t_{d(off)}$	Turn-off Delay time		-	88	-	
T_f	Turn-off Fall time		-	21	-	

Electrical Characteristics of Si MOSFET

Symbol	Parameter	Test Condition	Numerical		Unit
			Typ.	Max.	
$R_{\theta JC}$	Thermal Resistance, Junction to Case		1.3	-	℃/W
R_g	Gate Resistance	V_{GS} = 0V, f = 1.0㎒	2.1	-	Ω
C_{iss}	Input Capacitance	V_{DS} = 40V, V_{GS} = 0V, f = 1.0㎒	4396	-	pF
C_{oss}	Output Capacitance		511	-	
C_{rss}	Reverse Transfer Capacitance		30	-	
$Q_{g(tot)}$	Total Gate Charge at 10V	V_{DD} = 50V, I_D = 20A, $V_{GS(on)}$ = 10V	72	-	nC
Q_{gs}	Gate to Source Gate Charge		11	-	
Q_{gd}	Gate to Drain "Miller" Charge		14	-	

Electrical Characteristics of Si Diode

Symbol	Parameter	Test Condition	Numerical		Unit
			Typ.	Max.	
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	60	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	240	A
V_{SD}	Drain to Source Diode Forward Voltage	I_S = 20A, V_{GS} = 0V	0.8	1.2	V
T_{rr}	Reverse Recovery Time	I_F = 20A, V_{GS} = 0V, dI_F/dt=100A/㎲	69	-	ns
Q_{rr}	Reverse Recovery Charge		143	-	nC

Typical Characteristics

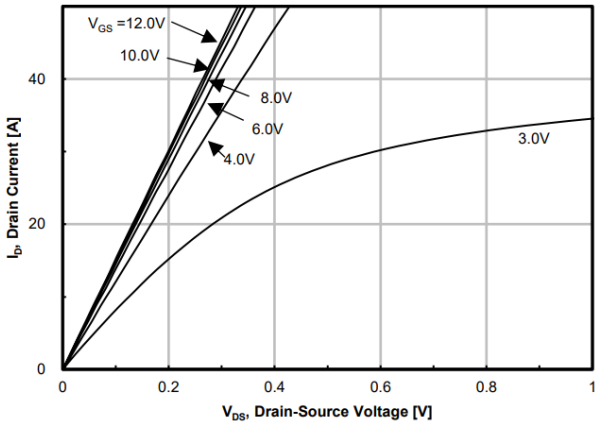


Figure 1. On-Region Characteristics

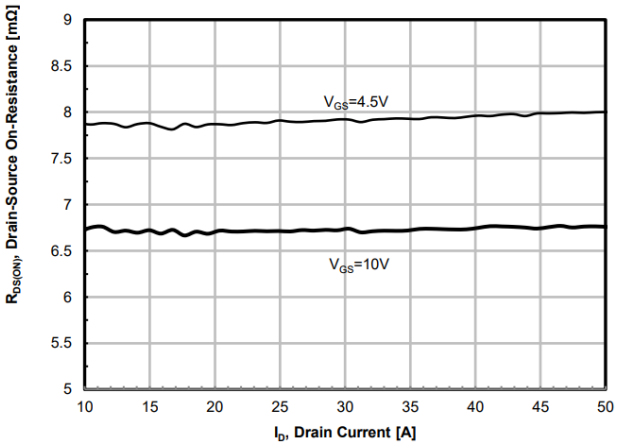


Figure 2. On-Resistance vs. Drain Current and Gate Voltage

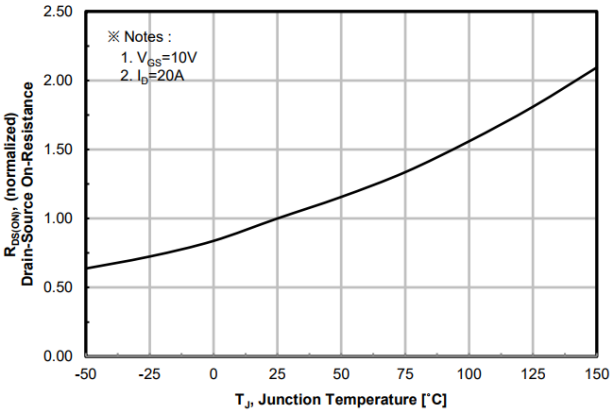


Figure 3. On Resistance vs. Junction Temperature

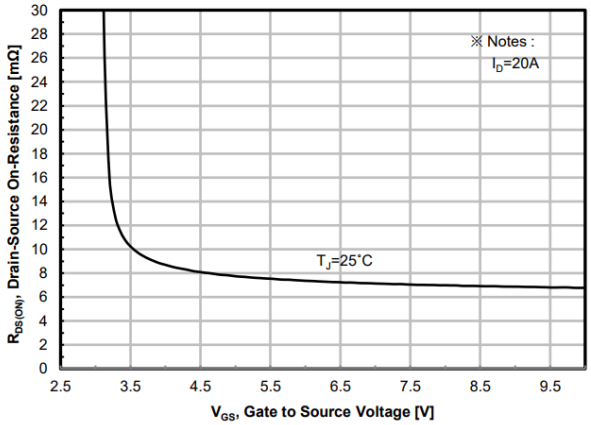


Figure 4. On-Resistance vs. Gate to Source Voltage

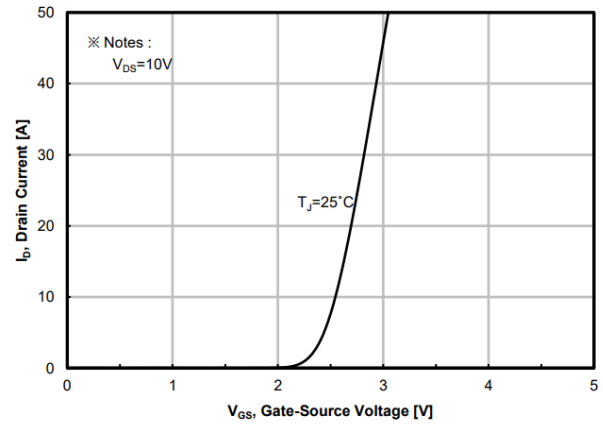


Figure 5. Transfer Characteristics

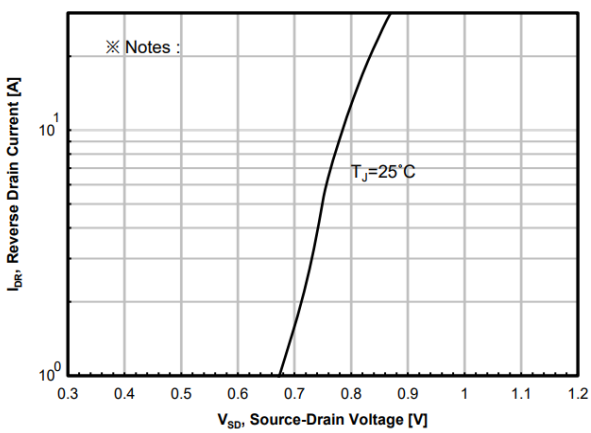


Figure 6. Source to Drain Diode Forward Voltage

Typical Characteristics

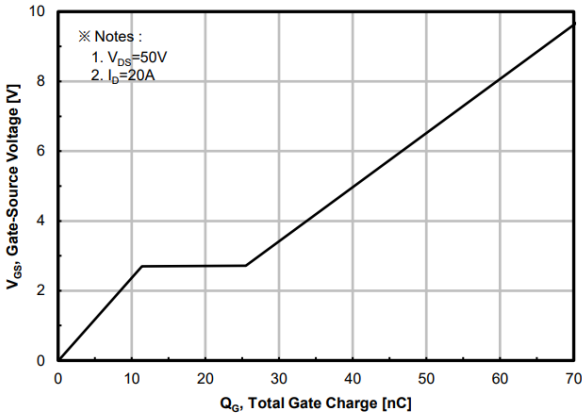


Figure 7. Gate Charge Characteristics

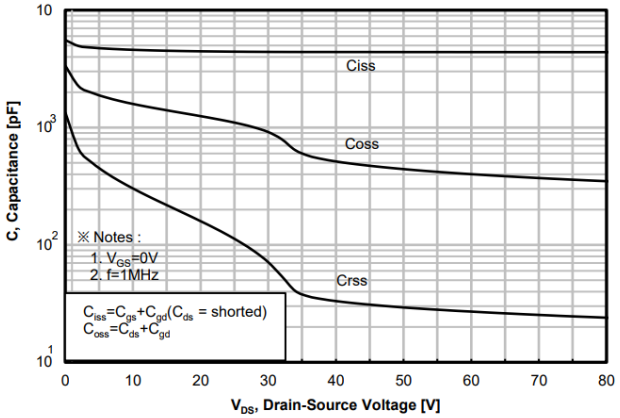


Figure 8. Capacitance Characteristics

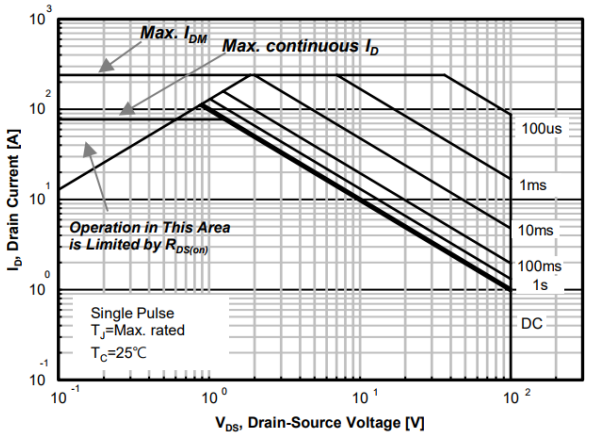


Figure 9. Maximum Safe Operating Area

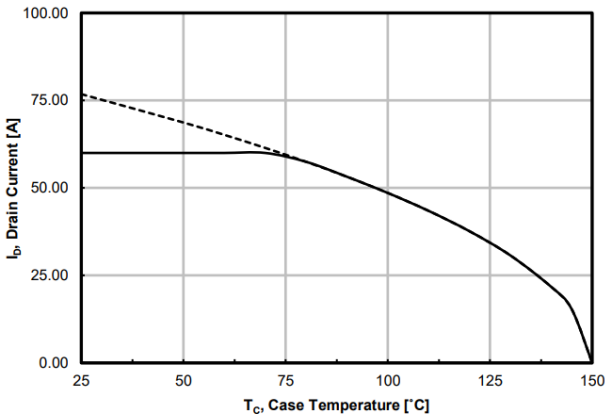


Figure 10. Maximum Drain Current vs. Case Temperature

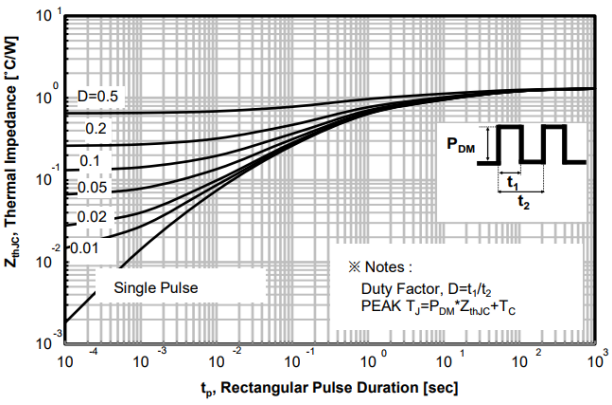
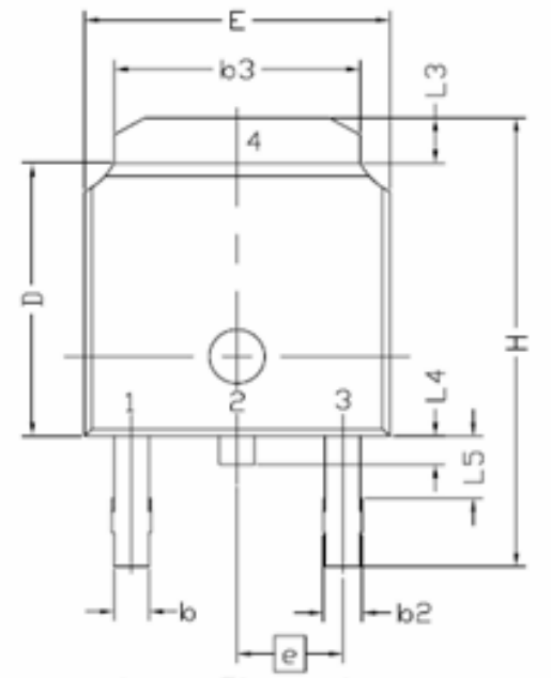
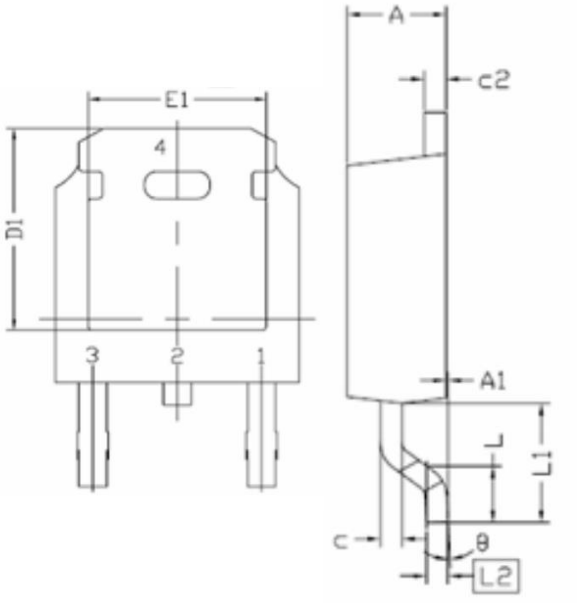


Figure 11. Transient Thermal Impedance, Junction to Ambient

Package Outline

Unit : mm





SYMBOL	DIMENSIONS			NOTES
	MIN	NOM	MAX	
E	6.34	6.54	6.74	
L	1.30	1.60	1.90	
L1	2.60	2.90	3.20	
L2		0.5 BSC		
L3	0.82	1.02	1.22	
L4	0.80	1.00	1.20	
L5	2.60	2.90	3.20	
D	5.80	6.10	6.40	
H	8.40	9.00	9.60	
b	1.42	1.52	1.62	
b2	2.35	2.55	2.75	
b3	5.20	5.30	5.40	
e		4.58 BSC		
A	2.08	2.28	2.48	
A1	0.00	0.15	-	
c	0.40	0.50	0.60	
c2	0.40	0.50	0.60	
D1	-	5.25	-	
E1	-	4.8	-	
θ	0.00°	10.00°		